

100 V dual-type N-channel MOSFET product with highly allowable power dissipation in a small package

“SSM6N815R” is 100 V dual-type N-channel MOSFET product featuring low On-resistance.

With its low On-resistance characteristics, power dissipation in the circuits can be reduced. And as a dual-type has been implemented in a TSOP6F package, the product can reduce its mounting area by about 40 % compared with a case where two single-type SOT-23F packages are used. It is suitable for applications such as LED lightings and LED drive circuits for LCD TVs that require both a high voltage and a small mounting area.



Features

- Low On-resistance
- Small package [2.9×2.8 mm (typ.)]
- Highly allowable power dissipation rating

Applications

- LED lightings
- LCD TVs
- Industrial equipment



LED lightings



LCD-TVs



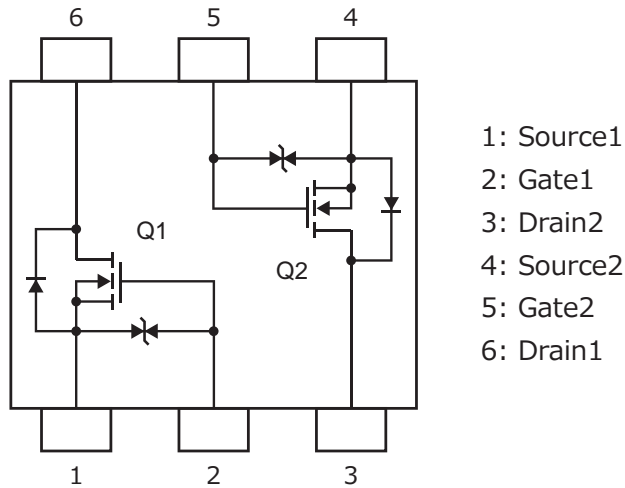
Industrial equipment

Product Specifications

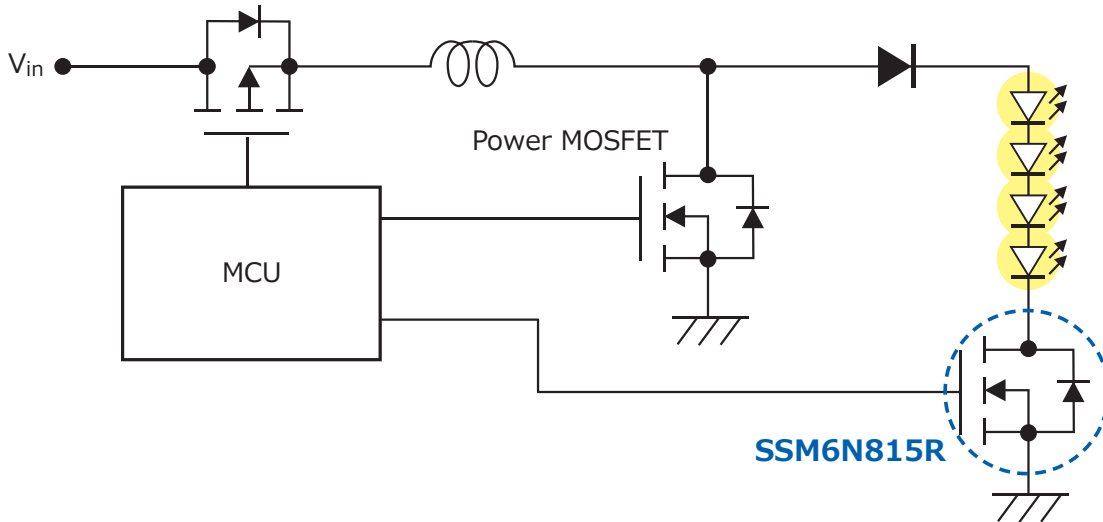
(@T_a=25°C)

Part number	Package	Absolute maximum ratings				Drain-source On-resistance R _{DS(ON)} typ. (mΩ)			Input capacitance C _{iss} typ. (pF)
		Drain-source voltage V _{DSS} (V)	Gate-source voltage V _{GSS} (V)	Drain current(DC) I _D (A)	Power dissipation P _D (W)	@V _{GS} = 4.0 V	@V _{GS} = 4.5 V	@V _{GS} = 10 V	
SSM6N815R	TSOP6F	100	±20	2.0	1.4	115	101	84	290

Pin Assignment

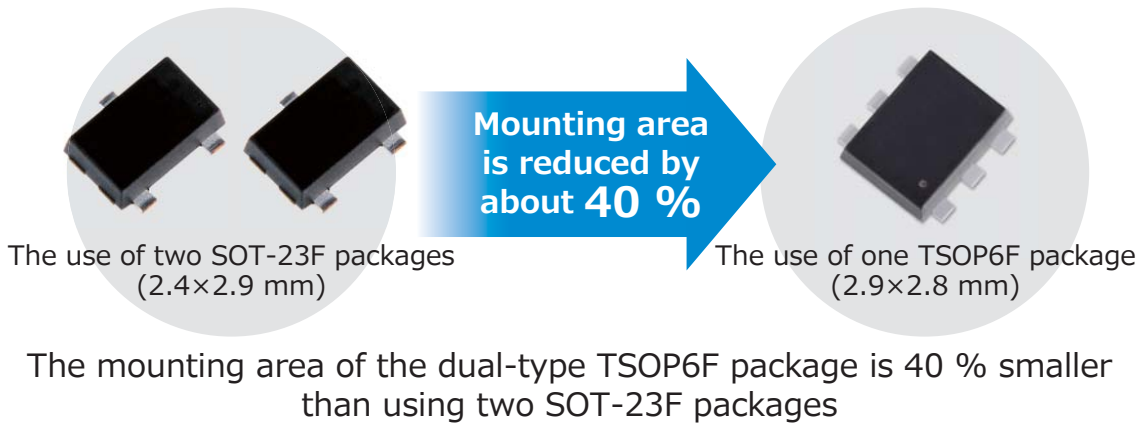


Application Circuit Example



The application circuits shown in this document are provided for reference purposes only. Thorough evaluation is required, especially at the mass-production design stage. Toshiba Electronic Devices & Storage Corporation does not grant any license to any industrial property rights by providing these examples of application circuits.

Comparison of Mounting Area



Before creating and producing designs and using, customers must also refer to and comply with the latest versions of all relevant information of this document and the instructions for the application that Product will be used with or for.